















ESD

TVS

MOS

LDO

Diode

Sensor

DC-DC

Product Specification

Domestic Part Number	AO3422A
Overseas Part Number	AO3422A
▶ Equivalent Part Number	AO3422A





N-Channel 60-V(D-S) MOSFET

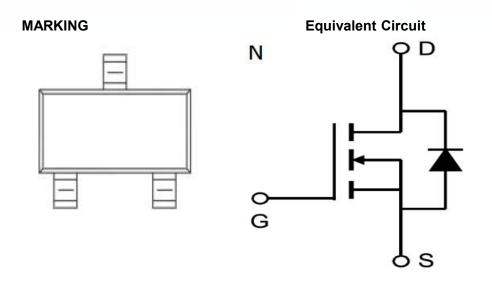
V(BR)DSS	RDS(on)MAX	ID
60 V	105mΩ@10V	2.14
	125mΩ@4.5V	2.1A

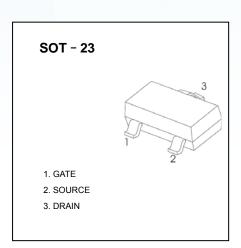
FEATURE

X TrenchFET Power MOSFET

APPLICATION

- X Load Switch for Portable Devices
- DC/DC Converter





Maximum ratings (Ta=25 $^{\circ}$ C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	VDS	60	V
Gate-Source Voltage	VGS	±20	V
Continuous Drain Current	ID	2.1	
Pulsed Diode Curren	IDM	10	Α
Continuous Source-Drain Current(Diode Conduction)	IS	0.85	
Power Dissipation	PD	1.25	W
Thermal Resistance from Junction to Ambient (t≤5s)	RθJA	125	°C/W
Operating Junction	TJ	150	$^{\circ}$
Storage Temperature	TSTG	-55~+150	$^{\circ}$



MOSFET ELECTRICAL CHARACTERISTICS

Static Electrical Characteristics (Ta = 25 $^{\circ}$ C Unless Otherwise Noted

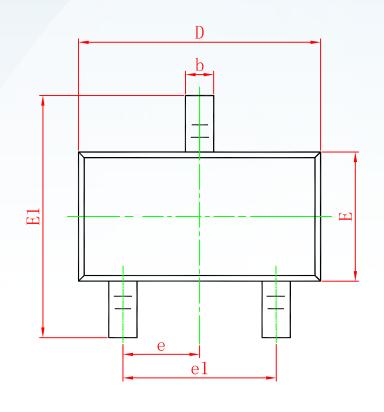
Parameter	Symbol	Test Condition	Min	Тур	Max	Unit
Static						
Drain-source breakdown voltage	V(BR)DSS	VGS = 0V, ID = 250μA	60			V
Gate-source threshold voltage	VGS(th)	VDS =VGS, ID = 250μA	1		2.5	V
Gate-source leakage	IGSS	VDS =0V, VGS = ±20V			±100	nA
Zero gate voltage drain current	IDSS	VDS = 60V, VGS =0V			1	μΑ
Drain-source on-state	DDS(on)	VGS = 10V, ID = 3A		80	105	mΩ
resistancea	RDS(on)	VGS = 4.5V, ID = 2A		89	125	mΩ
Forward transconductancea	gfs	VDS = 4.5V, ID = 2.1A		11		S
Diode forward voltage	VSD	IS=1.5A,VGS=0V		0.8	1.3	V
Dynamic						
Input capacitance	Ciss	VDS = 25V,VGS =0V, f=1MHz		214	300	pF
Output capacitance	Coss			31		pF
Reverse transfer capacitanceb	Crss			12.6		pF
Total gate charge	Qg			2.6	3.3	nC
Gate-source charge	Qgs	VDS = 25V,VGS = 4.5V, ID = 3A		0.6		nC
Gate-drain charge	Qgd	15 0/1		0.8		nC
Gate resistance	Rg	f=1MHz		1.3	3	Ω
Switchingb						
Turn-on delay time	td(on)			2.3		ns
Rise time	tr	VDS= 25V RL=6Ω, ID ≈ 1A, VGEN= 10V,Rg=3Ω		2.4		ns
Turn-off delay time	td(off)			16.5		ns
Fall time	tf	j		2		ns
Drain-source body diode characteristics						
Continuous Source-Drain Diode Current	IS	Tc=25°C			3	Α

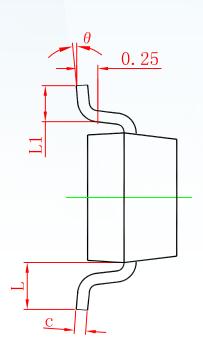
Note:

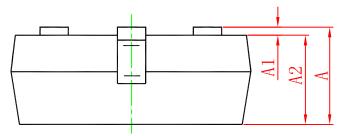
- 1. Repetitive Rating : Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t < 5 sec.
- 3. Pulse Test : Pulse Width≤300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production testing.



SOT-23 PACKAGE OUTLINE DIMENSIONS







Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min.	Max.	Min.	Max.	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950	TYP.	0.037	TYP.	
e1	1.800	2.000	0.071	0.079	
L	0.550	REF.	0.022	REF.	
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	



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